



HPD set-up tests of backside illuminated monolithic CMOS pixel sensor

V. Dulinski¹*, J.-D. Berst¹, A. Bream³, M. Caccia⁴, G. Claus¹, C.Colledani¹, G.Deptuch¹, D. Grandjean², Ch. Joram³, J. Seguinot³ , J.-L.Riester¹ and M. Winter²

LEPSI, 23 rue du Loess BP 20, 67037, Strasbourg Cedex 02, France
IReS, 23 rue du Loess BP 28, 67037, Strasbourg Cedex 02, France
CERN, CH-1211 Geneva 23, Switzerland
Universita degli Studi dell' Insubria, Como, Italy

Work supported under SUCIMA E.C. Contract N. G1RD-CT-2001-00561

Outlook

- <u>Application:</u> non-destructive beam monitor for hadron therapy beams
- <u>Device</u>: back-thinned monolithic CMOS pixel sensors
- <u>Qualification tests:</u> imaging of low energy electrons in HPD-like structure
- Conclusions





adrontherapy: use of a light ion beam for cancer irradiation

Effective use of a:





Cyclotron beam intensity fluctuation...

energy: $60 \div 250$ MeV p, $120 \div 400$ MeV/u $^{12}C^{6+}$ average intensity : 5 pA ($^{12}C^{6+}$) $\div 8.3$ nA (p) beam average cross section (4 σ): 10×10 mm²





Aim for a 'real-time', non destructive beam monitoring

efficient operation of the accelerator complex multiple measurements on the same beam maximum safety to the patient

No such a device exist on the market!





The solution: Secondary emission for Low Interception Monitoring (SLIM project)







SLIM development within SUCIMA Collaboration





P-BEAM MEASURED BY SLIM Scintillating screen + CCD camera





CMOS Monolithic Active Pixel Sensors (MAPS) principle

"From digital cameras to particle tracking device"



-The active volume (epi-layer, ~10 μm thick) is underneath the readout electronics, providing 100% fill factor

-The charge generated by ionization is collected by the n-well/p-epi diode

-Charge collection is achieved through the thermal diffusion

The device can be fabricated using a standard, cost effective and easily available twin-tub CMOS process on epi substrate. <u>No post-processing (e.g. bump-bonding)!</u>

System-on a chip approach possible





Requirements for electron imager

- -sensitivity to 20 keV electrons
- -active surface subdivided in 5000 cells (pads or pixels) or more;
- -dynamic range 3 to 10⁴ e-/pixel every 100 µs;
- -10 KHz frame rate (to guarantee ± 2 % dose uniformity);
- -no dead time



The final device in production...





...demonstration of back-thinning and electrons imaging using existing device







Standard calibration using 5.9 keV photons from ⁵⁵Fe source





IWORID-2004, Glasgow



HPD test set-up at CERN



Simplified view of vacuum pot with proximity focusing optics HPD using CsI photocathode



IWORID-2004, Glasgow



HPD test set-up at CERN







Spectrum of electrons emitted by photocathode

▶ 15kV



Reconstructed signal clusters





Spectrum of electrons emitted by photocathode

▶7.5kV



Reconstructed signal clusters





Voltage dependence of a signal

▶ 7.5kV – 20kV



>> Linear dependence « signal magnitude v.s. accelerating voltage »; x-axis intercept at 2.48kV!





Conclusions

- Novel back-thinning procedure successfully demonstrated on Mimosa5 CMOS monolithic pixel device
- Tests using HPD set-up confirm its low energy detection capabilities
- Final CMOS pixel prototype for SLIM/TERA in production
- Many new new application of the this device considered

Many thanks to <u>Laura Badano</u> and <u>Ornella Ferrando</u>, SUCIMA/TERA team members, for supplying me with all transparencies explaining SLIM idea and showing the first beam spot recorded with this device.